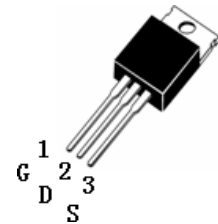
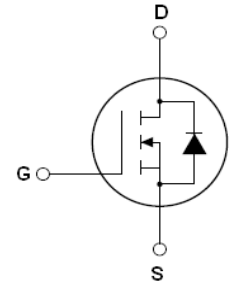


Feathers:

- Advanced trench process technology
- Special designed for Convertors and power controls
- High density cell design for ultra low Rdson
- Fully characterized Avalanche voltage and current
- Avalanche Energy 100% test

ID =15A
BV=100V
Rdson=0.06Ω (Typ.)


Description:

The SSF1090 is a new generation of high voltage and low current N-Channel enhancement mode trench power MOSFET. This new technology increases the device reliability and electrical parameter repeatability. SSF1090 is assembled in high reliability and qualified assembly house.

Application:

- Power switching application

SSF1090 TOP View (TO-220)

Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D@T_c=25\text{ C}$	Continuous drain current, VGS@10V	15	A
$I_D@T_c=100\text{ C}$	Continuous drain current, VGS@10V	10	
I_{DM}	Pulsed drain current ①	60	
$P_D@T_c=25\text{ C}$	Power dissipation	42	W
	Linear derating factor	0.4	W/C
V_{GS}	Gate-to-Source voltage	±20	V
E_{AS}	Single pulse avalanche energy ②	240	mJ
E_{AR}	Repetitive avalanche energy	TBD	mJ
dv/dt	Peak diode recovery voltage	28	v/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +175	°C

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-case	—	3.6	—	C/W
$R_{\theta JA}$	Junction-to-ambient	—	—	69	

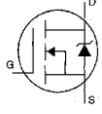
*When mounted on the minimum pas size recommended (PCB Mount)

Electrical Characteristics @TJ=25 °C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-to-Source breakdown voltage	100	—	—	V	$V_{GS}=0V, I_D=250\mu A$
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	0.06	0.09	Ω	$V_{GS}=10V, I_D=2A$
$V_{GS(th)}$	Gate threshold voltage	2.0	—	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
I_{DSS}	Drain-to-Source leakage current	—	—	1	μA	$V_{DS}=30V, V_{GS}=0V$
		—	—	10		$V_{DS}=100V, V_{GS}=0V, T_J=150\text{ C}$
I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	$V_{GS}=20V$

	Gate-to-Source reverse leakage	—	—	-100		$V_{GS}=-20V$
Q_g	Total gate charge	—	21.18		nC	$I_D=9.2A, V_{GS}=10V$ $V_{DD}=80V, R_L=8.6\Omega$
Q_{gs}	Gate-to-Source charge	—	4.7	—		
Q_{gd}	Gate-to-Drain("Miller") charge	—	8.5	—		
$t_{d(on)}$	Turn-on delay time	—	10		nS	$V_{DD}=50V$ $I_D=9.2A, R_L=5.4\Omega$ $R_G=18\Omega$ $V_{GS}=10V$
t_r	Rise time	—	9.5			
$t_{d(off)}$	Turn-Off delay time	—	18.3			
t_f	Fall time	—	4.2			
C_{iss}	Input capacitance	—	697	750	pF	$V_{GS}=0V$ $V_{DS}=25V$ $f=1.0MHZ$
C_{oss}	Output capacitance	—	59	110		
C_{rss}	Reverse transfer capacitance	—	43	45		

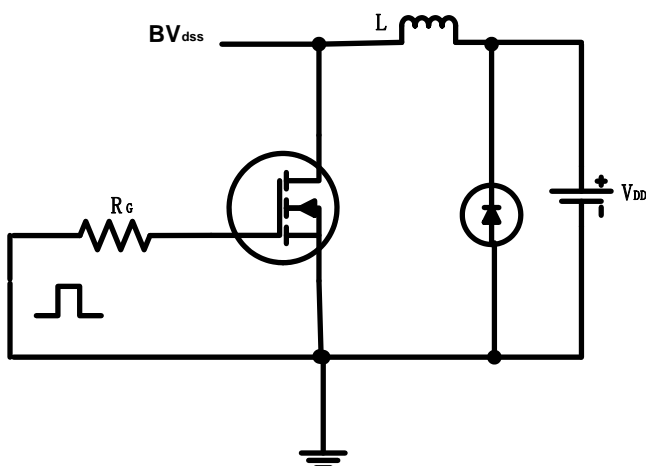
Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	18		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J=25^\circ C, I_S=3A, V_{GS}=0V$ ③
t_{rr}	Reverse Recovery Time	—	35	—	nS	$T_J=25^\circ C, I_F=9.2A$ $di/dt=100A/\mu s$ ③
Q_{rr}	Reverse Recovery Charge	—	67.2	—	μC	
t_{on}	Forward Turn-on Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

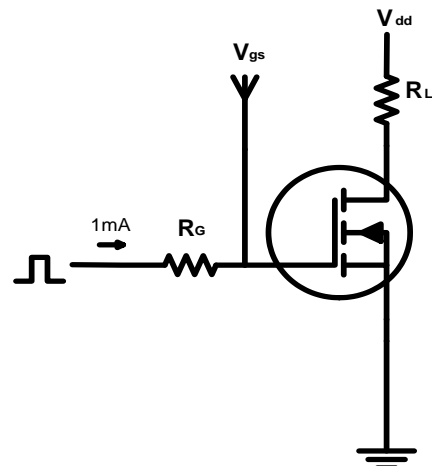
Notes:

- ① Repetitive rating; pulse width limited by max junction temperature
- ② Test condition: $L = 30mH, V_{DD} = 50V, I_D=4A$
- ③ Pulse width $\leq 300\mu s$, duty cycle $\leq 1.5\%$; $R_G = 25\Omega$ Starting $T_J = 25^\circ C$

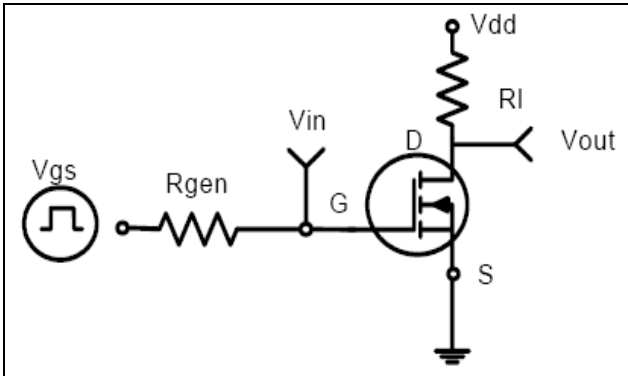
EAS Test Circuit:



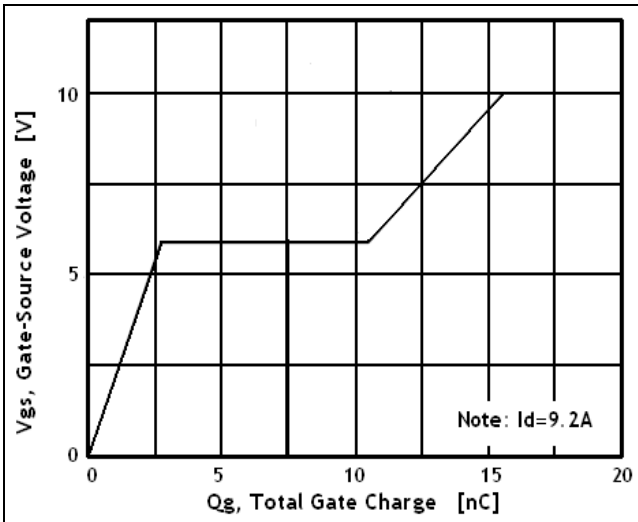
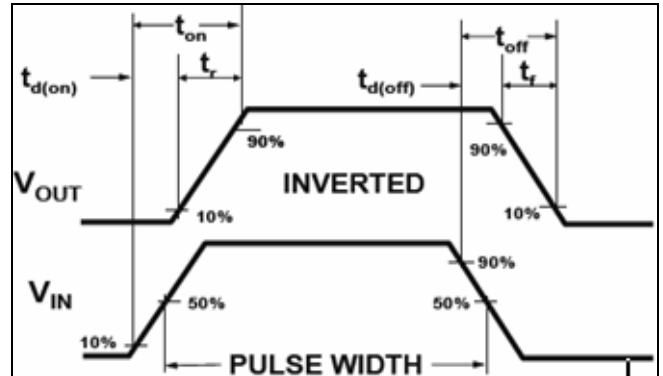
Gate Charge Test Circuit:



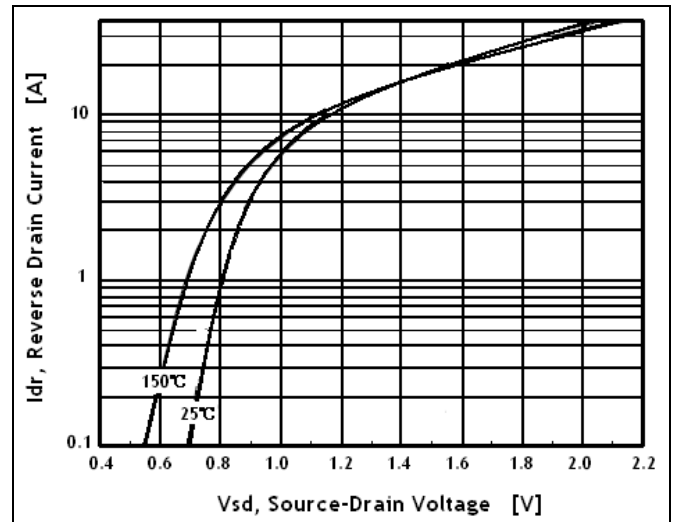
Switch Time Test Circuit:



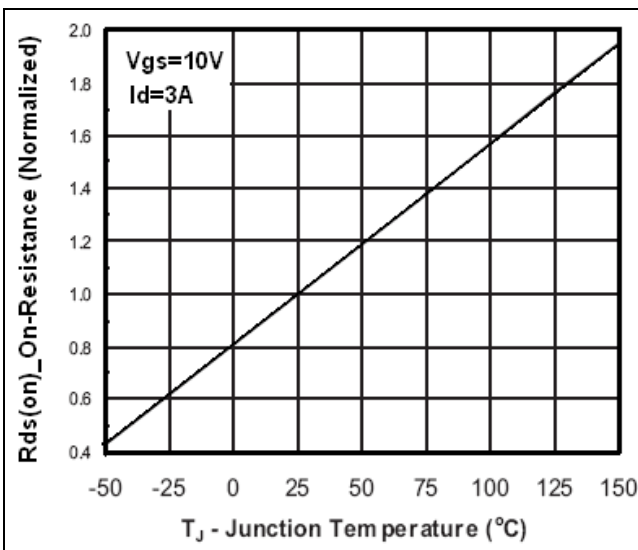
Switch Waveform:



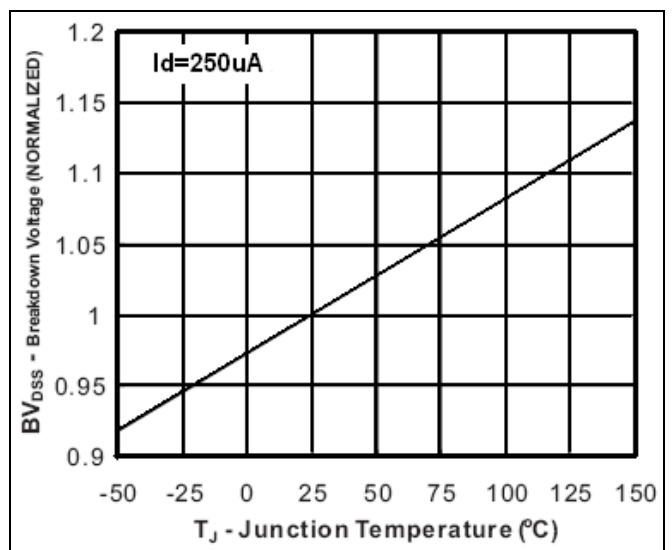
Gate Charge



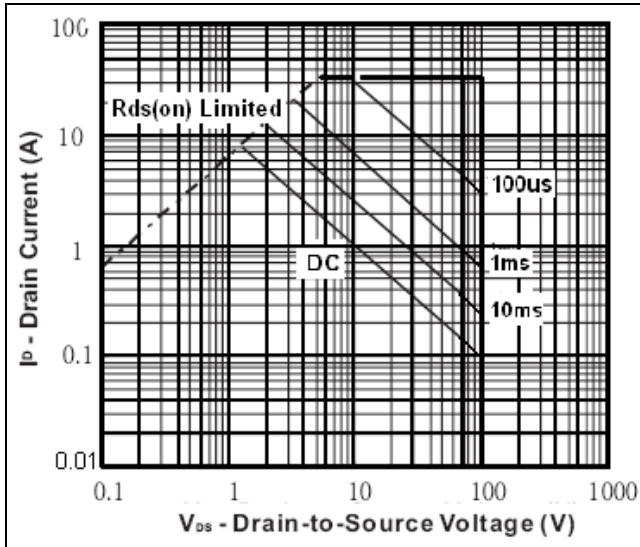
Source-Drain Diode Forward Voltage



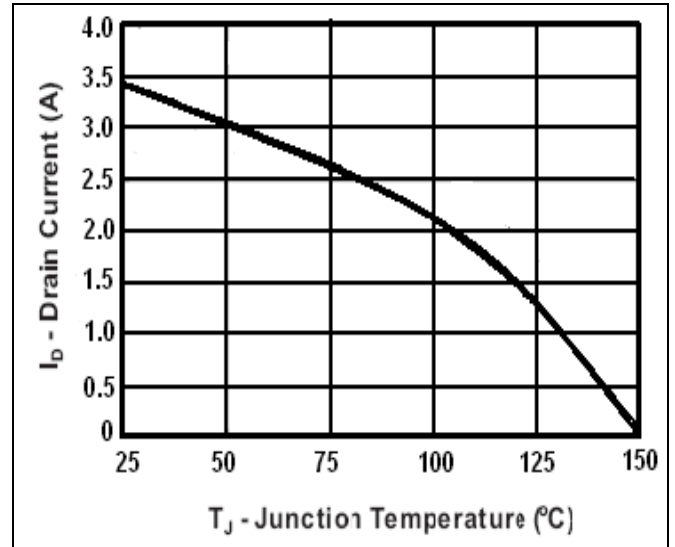
On Resistance vs. Junction Temperature



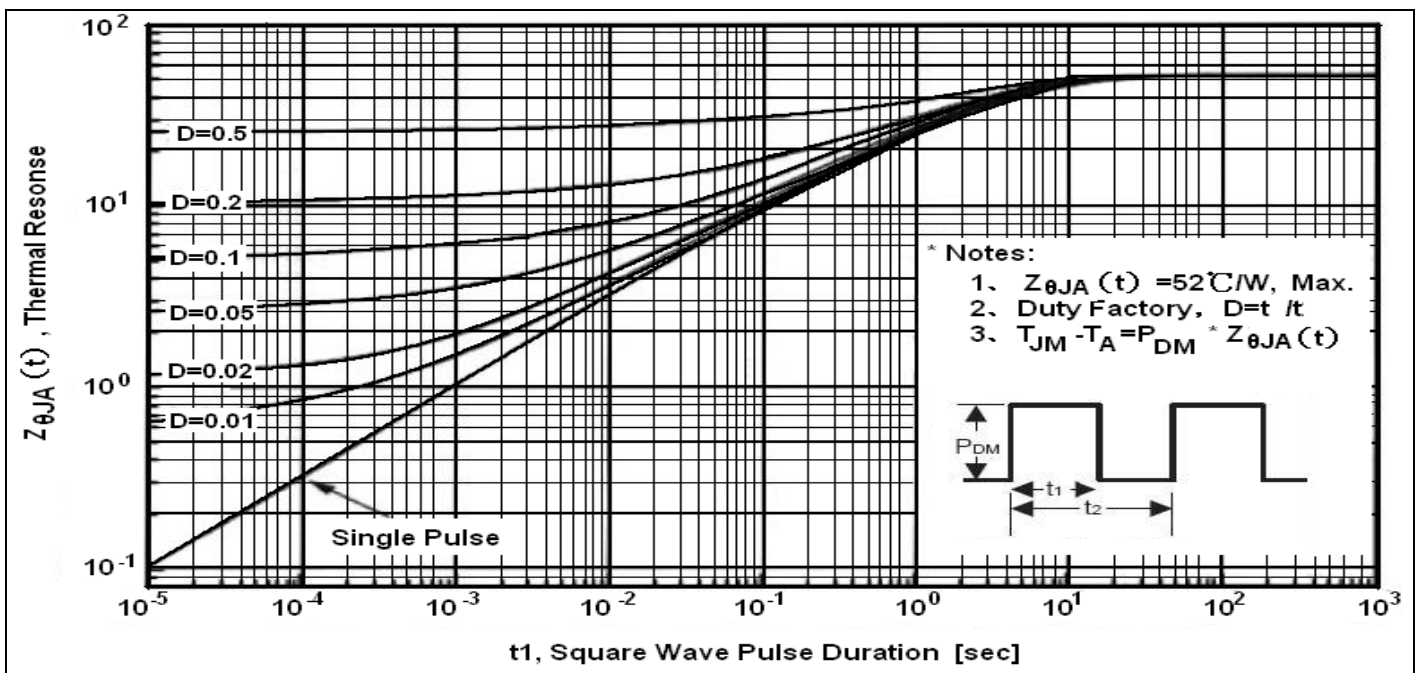
Breakdown Voltage vs. Junction Temperature



Safe Operation Area

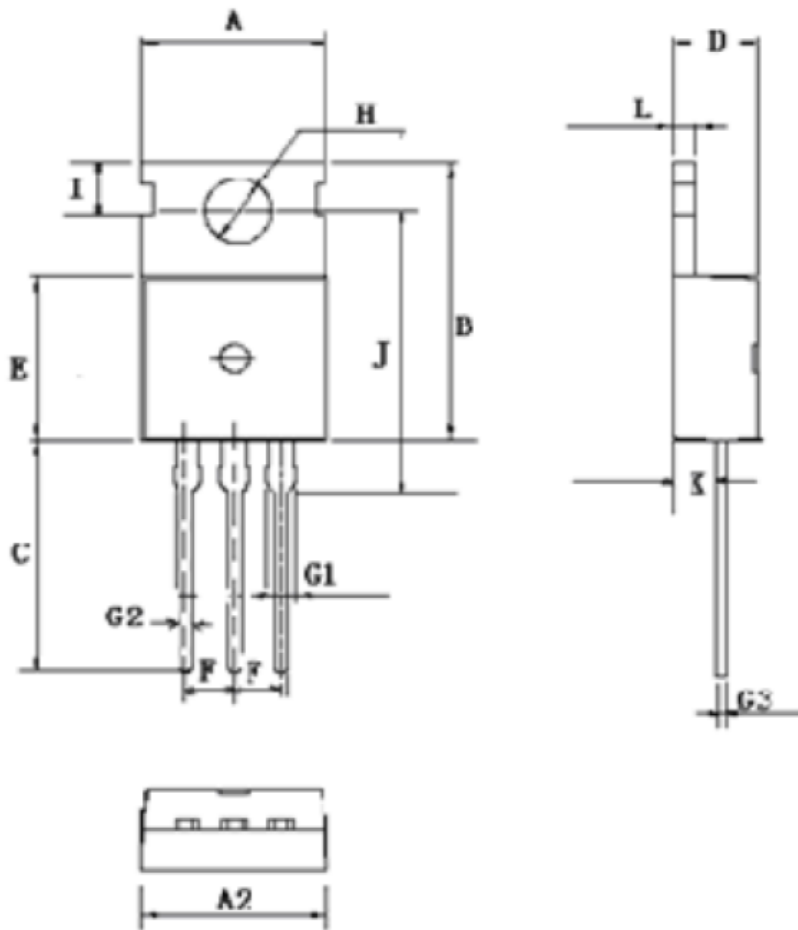


Max Drain Current vs. Junction Temperature



Transient Thermal Impedance Curve

TO220 MECHANICAL DATA:



TO-220 3L

图形对应符号	产品外形尺寸
A(mm)	9.66~10.28
A2(mm)	9.80~10.20
B(mm)	15.6~15.8
C(mm)	12.70~14.27
D(mm)	4.30~4.70
E(mm)	8.59~9.40
F(mm)	2.54 (nom)
G1(mm)	1.42~1.62
G2(mm)	0.70~0.95
G3(mm)	0.45~0.60
H(mm) dia.	3.50~3.70
I(mm)	2.7~2.9
J(mm)	15.70~16.25
K(mm)	2.20~2.90
L(mm)	1.15~1.40
M(mm)	0.5